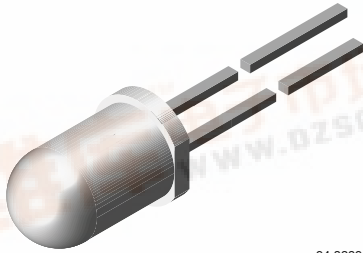




TSFF6210

Vishay Semiconductors

High Speed Infrared Emitting Diode, RoHS Compliant, 870 nm, GaAIAs Double Hetero



94 8389

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Peak wavelength: $\lambda_p = 870$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 10^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 24$ MHz
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

TSFF6210 is an infrared, 870 nm emitting diode in GaAIAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

APPLICATIONS

- Infrared video data transmission between Camcorder and TV set
- Free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Smoke-automatic fire detectors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSFF6210	180	± 10	870	15

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSFF6210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	1	A
Power dissipation		P_V	180	mW



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ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^{\circ}\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

Note

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

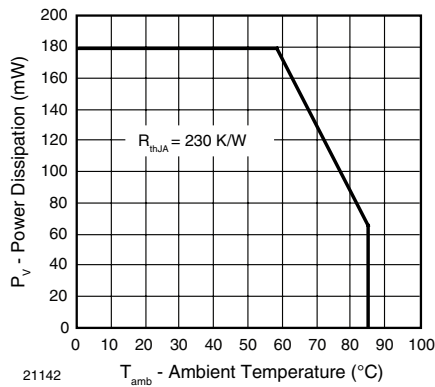


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

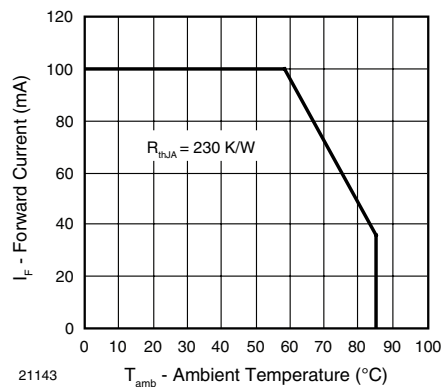


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100$ mA, $t_p = 20$ ms	V_F		1.5	1.8	V
	$I_F = 1$ A, $t_p = 100$ μs	V_F		2.3	3.0	V
Temperature coefficient of V_F	$I_F = 1$ mA	TK_{V_F}		- 1.8		mV/K
Reverse current	$V_R = 5$ V	I_R			10	μA
Junction capacitance	$V_R = 0$ V, $f = 1$ MHz, $E = 0$	C_j		125		pF
Radiant intensity	$I_F = 100$ mA, $t_p = 20$ ms	I_e	90	180	450	mW/sr
	$I_F = 1$ A, $t_p = 100$ μs	I_e		1800		mW/sr
Radiant power	$I_F = 100$ mA, $t_p = 20$ ms	ϕ_e		50		mW
Temperature coefficient of ϕ_e	$I_F = 100$ mA	$\text{TK}\phi_e$		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	$I_F = 100$ mA	λ_p		870		nm
Spectral bandwidth	$I_F = 100$ mA	$\Delta\lambda$		40		nm
Temperature coefficient of λ_p	$I_F = 100$ mA	$\text{TK}\lambda_p$		0.25		nm/K
Rise time	$I_F = 100$ mA	t_r		15		ns
Fall time	$I_F = 100$ mA	t_f		15		ns
Cut-off frequency	$I_{\text{DC}} = 70$ mA, $I_{\text{AC}} = 30$ mA pp	f_c		24		MHz
Virtual source diameter		d		3.7		mm

Note

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified



BASIC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

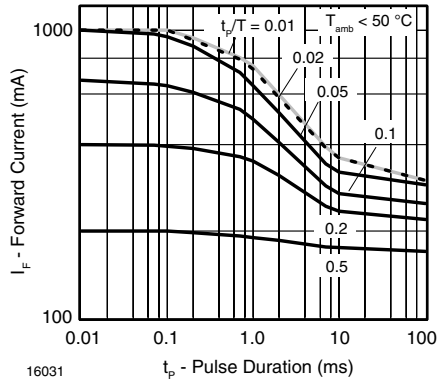


Fig. 3 - Pulse Forward Current vs. Pulse Duration

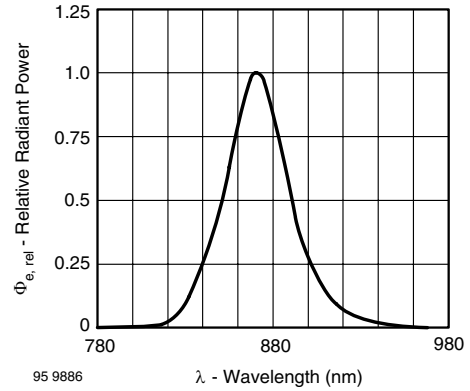


Fig. 6 - Relative Radiant Power vs. Wavelength

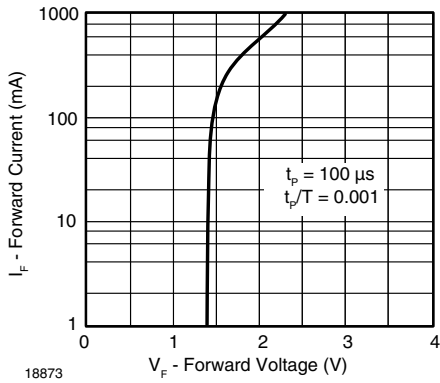


Fig. 4 - Forward Current vs. Forward Voltage

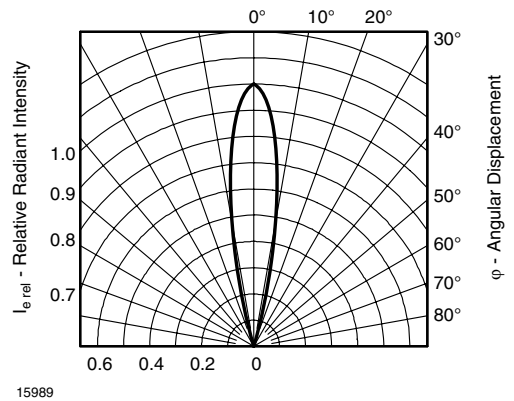


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

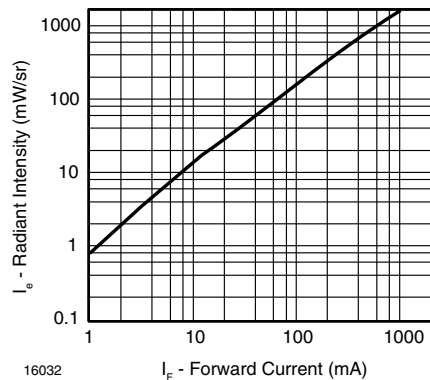


Fig. 5 - Radiant Intensity vs. Forward Current

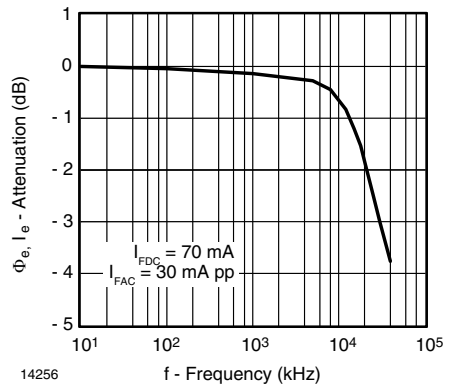


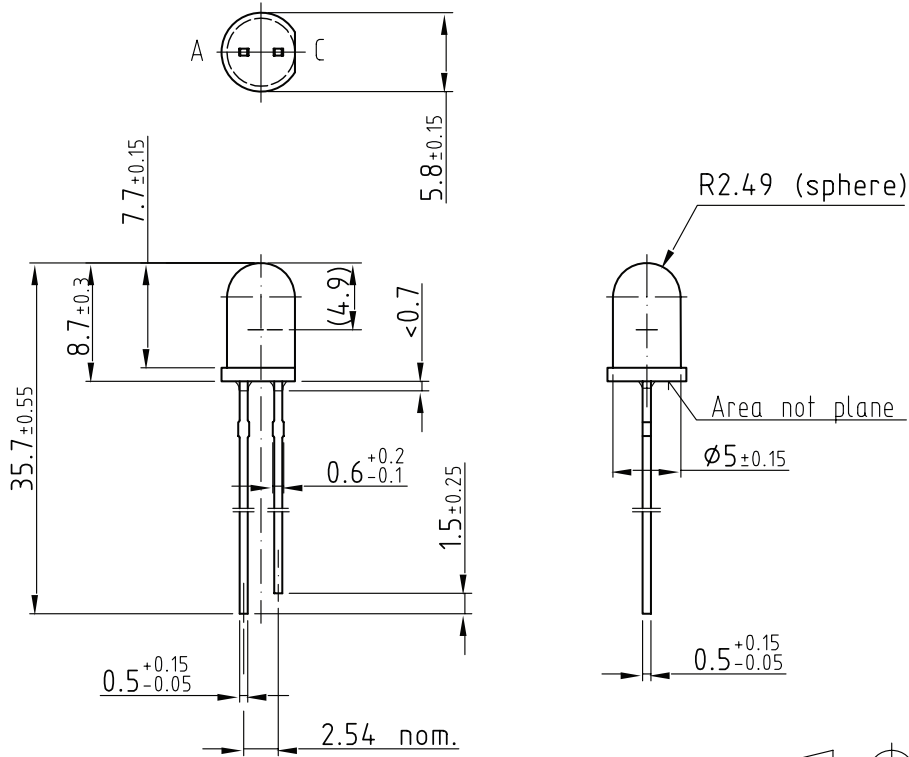
Fig. 8 - Attenuation vs. Frequency

TSFF6210

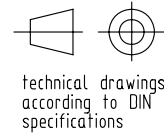


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PACKAGE DIMENSIONS in millimeters



6.544-5259.09-4
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20161





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